

Application No. 09/844,251

Filed: April 27, 2001

TC Art Unit: 2832

Confirmation No.: 8919

AMENDMENT TO THE CLAIMS

1 - 11. (Canceled)

12. (Previously presented) A process for manufacturing a contact on a microswitch prior to operation of the microswitch, the process providing a reduced resistance for the microswitch that is maintainable for many cycles when the microswitch is operated, comprising:

a. forming the microswitch contact with a predetermined material;

b. exposing the microswitch contact to a fluid that operates in conjunction with the predetermined material to lower a contact resistance, the exposure to the fluid being over an interval that ends prior to operation of the microswitch; and

wherein the fluid comprises materials selected from the group consisting of oxygen, carbon tetrafluoride, sulfur hexafluoride or other fluorine-containing gases, argon and mixtures thereof.

13. (Previously presented) The process of claim 12 wherein the fluid is a gaseous plasma.

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14. (Previously presented) The process of claim 13 wherein the plasma is Inductively Coupled Plasma.

15 - 19. (Canceled)

20. (Previously presented) A semiconductor package having a semiconductor die connected to external pins, the die including an active area;

a microswitch formed on a surface of the die, wherein a microswitch contact is formed with a process for reducing a resistance of the microswitch and maintaining a low resistance of the microswitch for many cycles, comprising:

a. forming the microswitch contact with a predetermined material;

b. temporarily exposing the microswitch contact to a fluid that operates in conjunction with the predetermined material to lower a contact resistance.